Chinkyo Kim

List of Publications by Year
in descending order

30 papers	137 citations	1478505 6 h-index	1474206 9 g-index
32 all docs	32 docs citations	32 times ranked	128 citing authors

#	Article	IF	Citations
1	Nitridation- and Buffer-Layer-Free Growth of $[1ar{1}00]$-Oriented GaN Domains on m-Plane Sapphire Substrates by Using Hydride Vapor Phase Epitaxy. Applied Physics Express, 2012, 5, 121001.	2.4	12
2	A surface flattening mechanism of a heteroepitaxial film consisting of faceted non-flat top twins: [11Â¯3Â¯]-oriented GaN films grown on <i>m</i>-plane sapphire substrates. Applied Physics Letters, 2014, 104, .	3.3	10
3	Self-regulated in-plane polarity of [11Â¯00]-oriented GaN domains coalesced from twins grown on a SiO2-patterned <i>m</i>-plane sapphire substrate. Applied Physics Letters, 2014, 104, .	3.3	9
4	Surface-morphology evolution and strain relaxation during heteroepitaxial growth of GaN films without low-temperature nucleation layers. Applied Physics Letters, 2007, 90, 151905.	3.3	8
5	Use of Polytypes to Control Crystallographic Orientation of GaN. Crystal Growth and Design, 2010, 10, 5307-5311.	3.0	8
6	Polarity-inverted lateral overgrowth and selective wet-etching and regrowth (PILOSWER) of GaN. Scientific Reports, 2018, 8, 4112.	3.3	7
7	Controlled growth and surface morphology evolution of m-oriented GaN faceted-domains on SiO2-patterned m-plane sapphire substrates. Applied Physics Letters, 2010, 97, .	3.3	6
8	Spontaneous inversion of in-plane polarity of<i>a</i>-oriented GaN domains laterally overgrown on patterned<i>r</i>-plane sapphire substrates. Journal of Applied Crystallography, 2013, 46, 443-447.	4.5	6
9	Spontaneous transition in preferred orientation of GaN domains grown on r-plane sapphire substrate from [112Â¯0] to [0001]. Applied Physics Letters, 2009, 94, 102103.	3.3	5
10	Microstructural Analysis of Void Formation Due to a NH4Cl Layer for Self-Separation of GaN Thick Films. Crystal Growth and Design, 2009, 9, 2877-2880.	3.0	5
11	Non-edge-triggered inversion from Ga polarity to N polarity of <i>c</i>-GaN domains on an SiO₂ mask during epitaxial lateral overgrowth. Journal of Applied Crystallography, 2019, 52, 532-537.	4.5	5
12	Nucleation characteristics of GaN nanorods grown on etched sapphire substrates by hydride vapor phase epitaxy. Journal of Crystal Growth, 2009, 311, 2953-2955.	1.5	4
13	Novel approach to the fabrication of a strain- and crack-free GaN free-standing template: Self-separation assisted by the voids spontaneously formed during the transition in the preferred orientation. Journal of Crystal Growth, 2010, 312, 198-201.	1.5	4
14	Analysis of Morphological Evolution of Crystalline Domains in Nonequilibrium Shape by Using Minimization of Effective Surface Energy. Crystal Growth and Design, 2011, 11, 3930-3934.	3.0	4
15	Spontaneous pattern transfer and selective growth of graphene on a Cu foil. Carbon, 2015, 82, 238-244.	10.3	4
16	Inversion domain boundary structure of laterally overgrown c-GaN domains including the inversion from Ga to N polarity at a mask pattern boundary. Journal of Applied Crystallography, 2018, 51, 1551-1555.	4.5	4
17	Polarity and threading dislocation dependence of the surface morphology of <i>c</i>-GaN films exposed to HCl vapor. Journal of Materials Chemistry C, 2018, 6, 6264-6269.	5.5	4
18	Accelerated surface flattening by alternating Ga flow in hydride vapor phase epitaxy. Journal of Crystal Growth, 2009, 311, 3025-3028.	1.5	3

#	Article	IF	Citations
19	Surface morphology of GaN nanorods grown by catalyst-free hydride vapor phase epitaxy. Applied Surface Science, 2009, 256, 1078-1081.	6.1	3
20	Microscopic analysis of thermally-driven formation of Cu-Si alloy nanoparticles in a Cu/Si template. Journal of the Korean Physical Society, 2013, 63, 2128-2132.	0.7	3
21	The determining factor of a preferred orientation of GaN domains grown on m-plane sapphire substrates. Scientific Reports, 2015, 5, 16236.	3.3	3
22	Faceted growth of ({f {overline 1}103})-oriented GaN domains on an SiO₂-patterned <i>m</i>-plane sapphire substrate using polarity inversion. Journal of Applied Crystallography, 2017, 50, 30-35.	4.5	3
23	A Laterally Overgrown GaN Thin Film Epitaxially Separated from but Physically Attached to an SiO₂-Patterned Sapphire Substrate. Crystal Growth and Design, 2020, 20, 6198-6204.	3.0	3
24	Effect of the Temperature Gradient Between a Substrate and its Ambient on the Growth of Vertically-Aligned GaN Nanorods. Journal of the Korean Physical Society, 2008, 53, 908-911.	0.7	3
25	Diffusion-enhanced preferential growth of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e570" altimg="si37.svg"><mml:mi>m</mml:mi></mml:math>-oriented GaN micro-domains on directly grown graphene with a large domain size on Ti/SiO2/Si(001). Materials Today Communications, 2022, 30, 103113.	1.9	3
26	Long-range ordering of GaN nano-grains grown on vicinal sapphire substrates. Journal of Crystal Growth, 2008, 310, 3278-3281.	1.5	2
27	Two-dimensional non-close-packed arrays of polystyrene microspheres prepared by controlling the size of polystyrene microspheres. Polymer, 2019, 185, 121938.	3.8	2
28	<i>Inâ€situ</i> measurement of the strain relaxation of GaN nanograins during Xâ€ray irradiation. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1699-1701.	0.8	1
29	Catalytic decomposition of SiO 2 by Fe and the effect of Cu on the behavior of released Si species. Current Applied Physics, 2016, 16, 93-100.	2.4	1
30	Branching Characteristics of GaN Multipods Grown by Using Hydride Vapor Phase Epitaxy. Journal of the Korean Physical Society, 2008, 53, 1393-1396.	0.7	1